

Description:

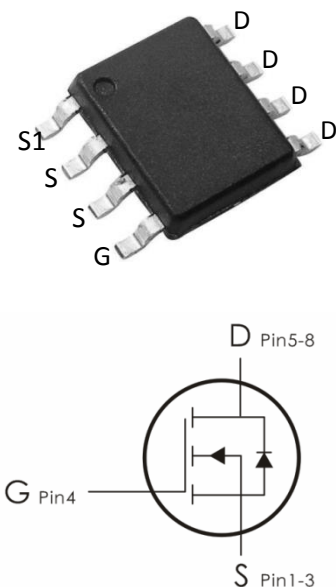
This N-Channel MOSFET uses advanced trench technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=60V, I_D=6A, R_{DS(ON)}<36m\Omega @V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
SE036NG-F	E036N-F	SOP-8	3000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current -Continuous ¹ ($T_A=25^{\circ}C$)	6	A
	Drain Current -Continuous ¹ ($T_A=70^{\circ}C$)	4.5	
I_{DM}	Drain Current – Pulsed ²	18	
E_{AS}	Single Pulse Avalanche Energy ³	22	mJ
I_{AS}	Avalanche Current	21	A
P_D	Power Dissipation ⁴ ($T_A=25^{\circ}C$)	1.5	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^{\circ}C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case ¹	25	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ¹	85	

Electrical Characteristics: ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	60	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V, T _J =25℃	---	---	1	uA
		V _{DS} =48V , V _{GS} =0V, T _J =55℃	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0V	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1	---	2.5	V
R _{DS(ON)}	Static Drain-Source On Resistance ²	V _{GS} =10V, I _D =4A	---	27	36	m Ω
		V _{GS} =4.5V, I _D =3A	---	35	46	m Ω
G _{FS}	Forward Transconductance	V _{DS} =5V, I _D =4A	---	28.3	---	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	1000	---	pF
C _{oss}	Output Capacitance		---	60	---	
C _{rss}	Reverse Transfer Capacitance		---	45	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} =30V, I _D =4A R _G =3.3 Ω , V _{GS} =10V	---	3	---	ns
t _r	Rise Time		---	34	---	ns
t _{d(off)}	Turn-Off Delay Time		---	23	---	ns
t _f	Fall Time		---	6	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =48V, I _D =4A	---	19	---	nC
Q _{gs}	Gate-Source Charge		---	2.6	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	4.1	---	nC
R _G	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	2.5	---	Ω
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25℃	---	---	1.2	V
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	4.5	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	18	A
T _{rr}	Body Diode Reverse Recovery Time	I _F =4A , di/dt=100A/μs ,	---	12.1	---	Ns
Q _{rr}	Body Diode Reverse Recovery Charge	T _J =25℃	---	6.7	---	Nc

Notes:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=21A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics: ($T_C=25^\circ C$ unless otherwise noted)

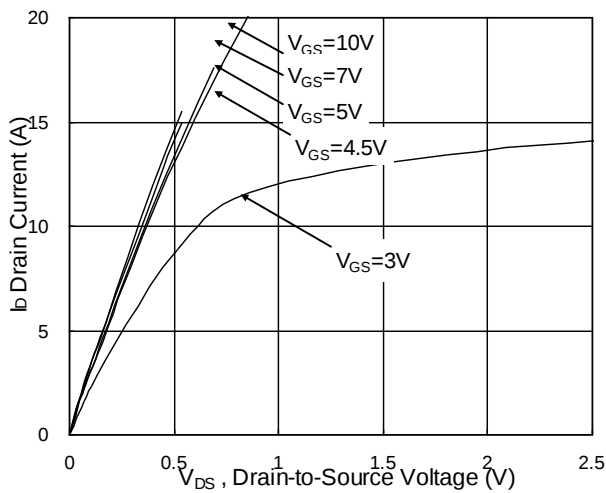


Fig.1 Typical Output Characteristics

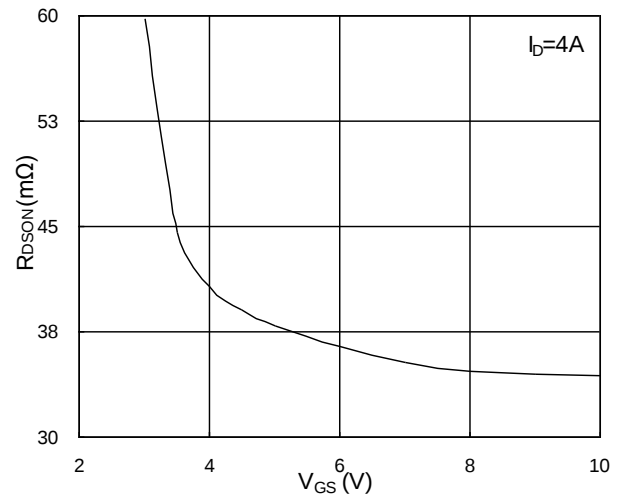


Fig.2 On-Resistance vs. Gate-Source

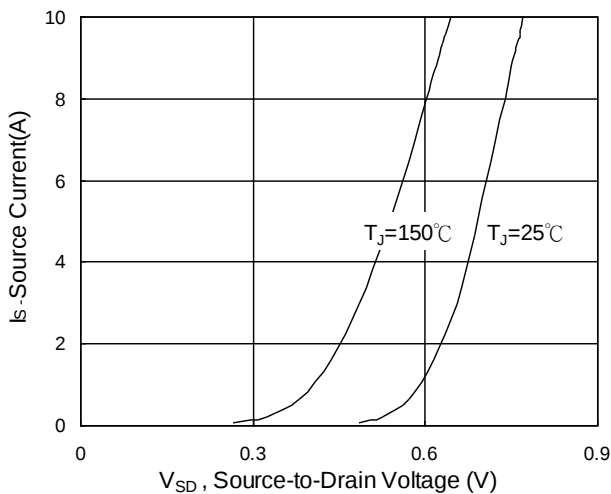


Fig.3 Forward Characteristics Of Reverse

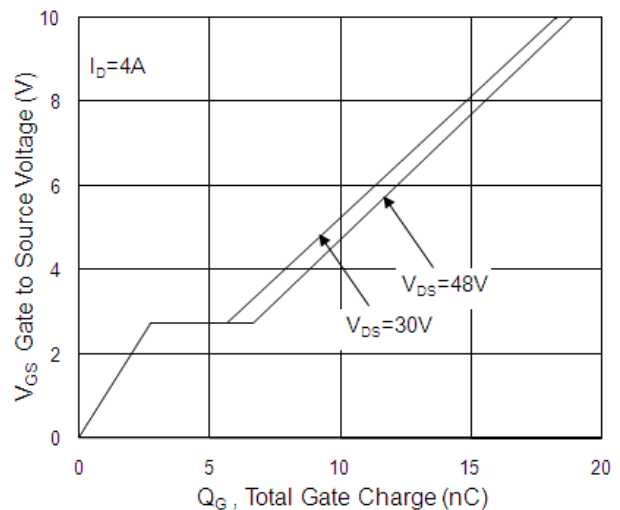


Fig.4 Gate-Charge Characteristics

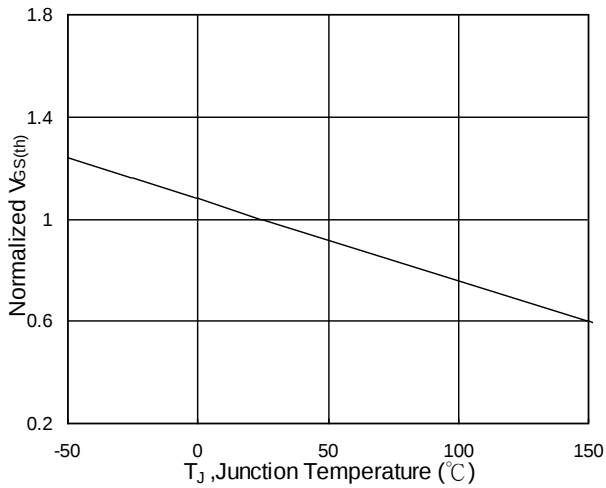


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

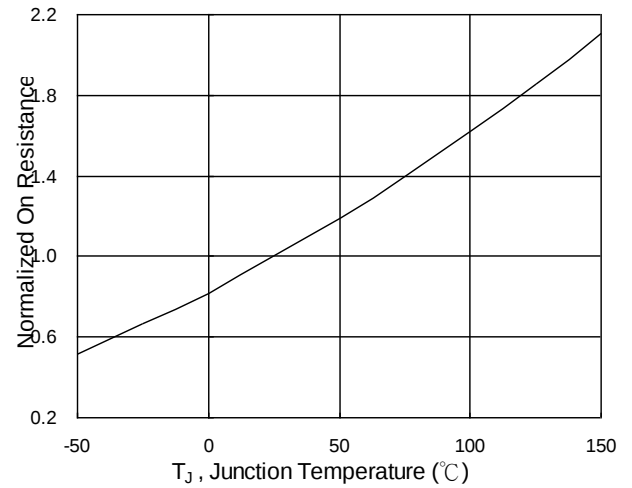


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

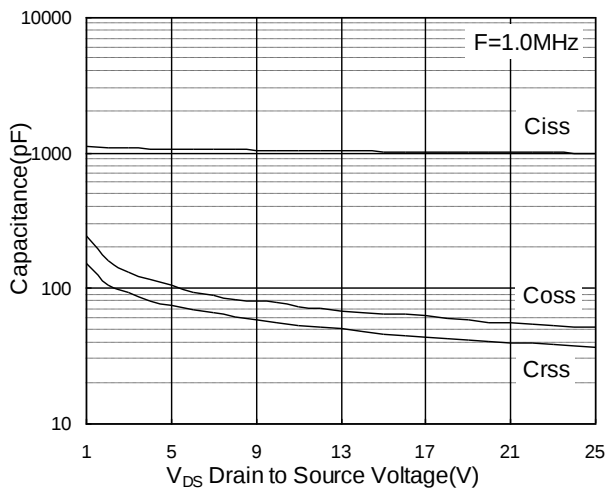


Fig.7 Capacitance

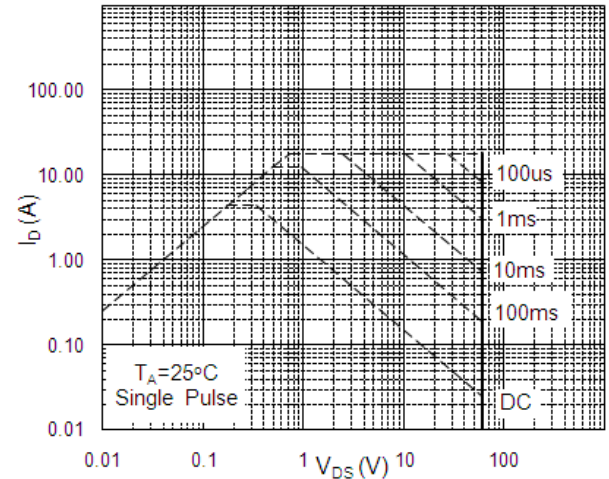


Fig.8 Safe Operating Area

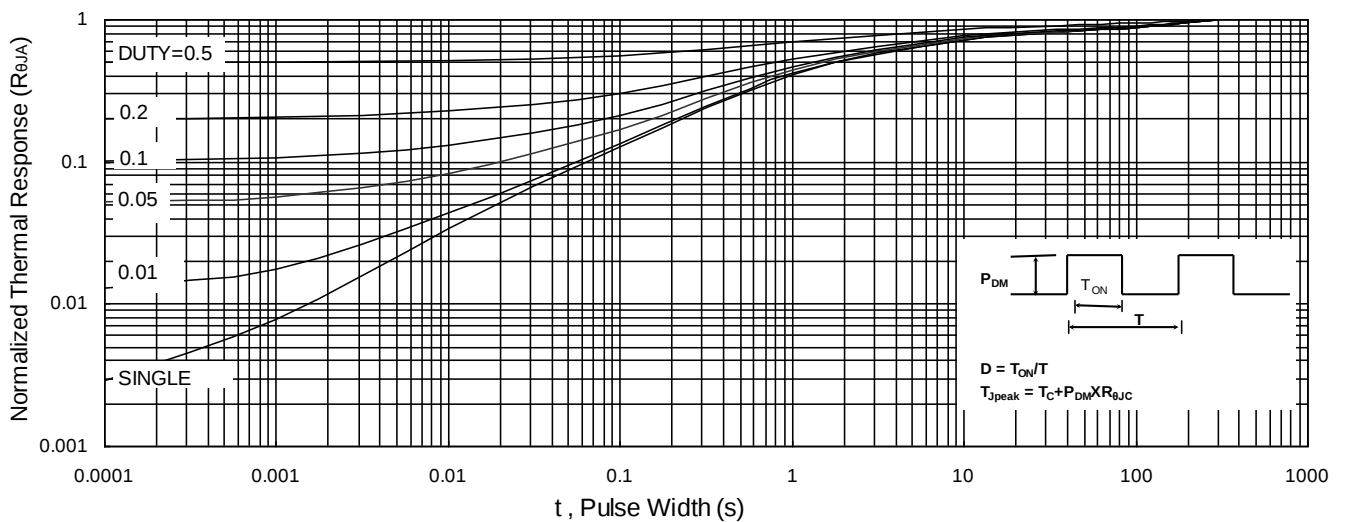
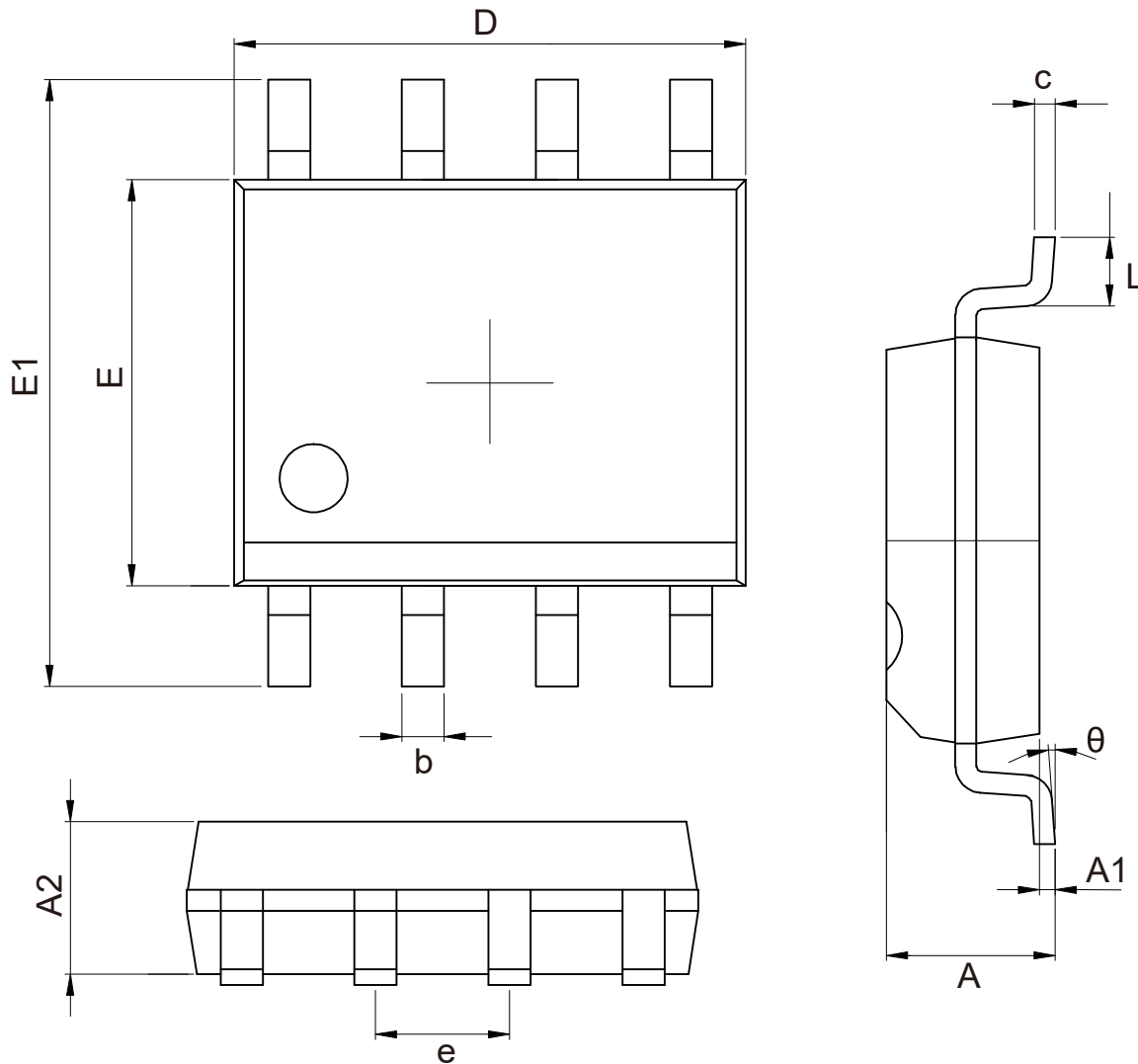


Fig.9 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information:



COMMON DIMENSIONS			
CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	1.350	—	1.750
A1	0.100	—	0.250
A2	1.350	—	1.550
b	0.330	—	0.510
c	0.170	—	0.250
D	4.700	—	5.100
E	3.800	3.900	4.000
E1	5.800	—	6.200
e	1.270BSC		
L	0.400	—	1.270
θ	0°	--	8°

Unit:mm

Marking Information:

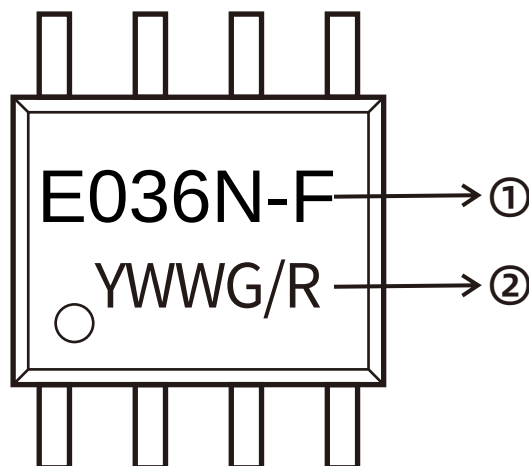
①. Part NO.

②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)



Attention :

- Information furnished in this document is believed to be accurate and reliable. However, Shenzhen Doingter Semiconductor Co.,Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it.
- Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Shenzhen Doingter complies with the agreement. Products and information provided in this document have no infringement of patents.
- Shenzhen Doingter assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.  Is a registered trademark of Shenzhen Doingter Semiconductor Co., Ltd. Copyright © 2013 Shenzhen Doingter Semiconductor Co.,Ltd. Printed All rights reserved.